

L Number	Hits	Search Text	DB	Time stamp
1	51947	semiconductor and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/15 16:54
2	12799	(semiconductor and dram) and (trench\$2 or recess\$2 or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/15 16:54
3	877	((semiconductor and dram) and (trench\$2 or recess\$2 or groove)) and nitride and liner	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/15 16:55
4	197	((semiconductor and dram) and (trench\$2 or recess\$2 or groove)) and nitride and liner) and collar and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/15 16:56
5	151	(((semiconductor and dram) and (trench\$2 or recess\$2 or groove)) and nitride and liner) and collar and oxide) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/15 16:56